# BYC58X-600

## 8 A hyperfast rectifier diode

Rev. 01 — 23 February 2010

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Hyperfast epitaxial rectifier diode in a SOD113 (2-lead TO-220F) plastic package specifically for use in CCM PFC applications for reduced switching losses.

#### 1.2 Features and benefits

- Allows use of smaller MOSFETs and heatsinks
- Isolated package
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET
- Superfast switching

#### 1.3 Applications

- Continuous Current Mode (CCM)
  Power Factor Correction (PFC)
- Desk top computer power supplies
- Flat panel TV power supplies
- Power supply adapters
- Server power supplies
- Telecom power supplies

### 1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	600	V
$I_{F(AV)}$	average forward current	square-wave pulse; $\delta = 0.5$ ; $T_h \le 93$ °C; see <u>Figure 1</u> and <u>2</u>	-	-	8	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; sine-wave pulse	-	-	110	Α
		$T_{j(init)}$ = 25 °C; $t_p$ = 8.3 ms; sine-wave pulse	-	-	120	Α
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	with heatsink compound; see Figure 3	-	2.5	3	K/W



Table 1. Quick reference ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
••	reverse recovery time	$I_F = 8 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; see Figure 6	-	12.5	-	ns
		$I_F = 8 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; see Figure 6 and 7	-	21	-	ns
Q <sub>r</sub>	recovered charge	$I_F = 8 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; see Figure 5 and 6	-	40	-	nC
Static ch	naracteristics					
V <sub>F</sub>	forward voltage	$I_F = 8 \text{ A}; T_j = 25 \text{ °C};$ see Figure 4	-	2.35	3.2	V
		$I_F = 8 \text{ A}; T_j = 150 \text{ °C};$ see <u>Figure 4</u>	-	2	2.4	V

## 2. Pinning information

Table 2. Pinning information

Table 2.	ı ııııııı	inormation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		v 14 .
2	Α	anode	mb	K — A 001aaa020
mb	n.c.	mounting base; isolated		
			SOD113 (TO-220F)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC58X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$I_{F(AV)}$	average forward current	square-wave pulse; $\delta$ = 0.5; $T_h \le 93$ °C; see Figure 1 and 2	-	8	Α
I <sub>FRM</sub>	repetitive peak forward current	square-wave pulse; $\delta$ = 0.5; $t_p$ = 25 $\mu$ s	-	16	Α
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	110	Α
	forward current	$t_p$ = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	120	Α
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

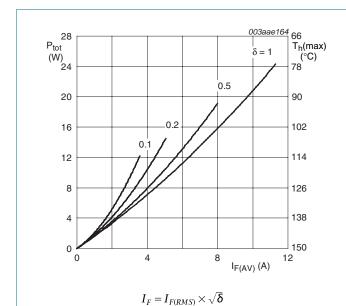


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

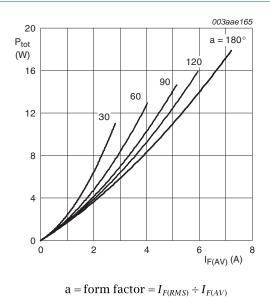
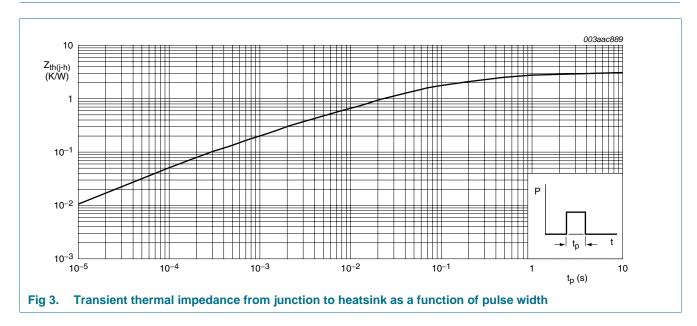


Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 3	-	2.5	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



### 6. Isolation characteristics

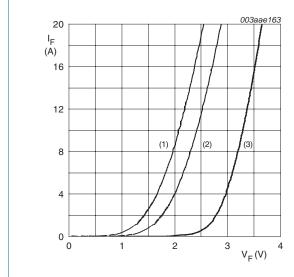
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static characteristics						
V <sub>F</sub>	forward voltage	$I_F = 8 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 4	-	2.35	3.2	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; see <u>Figure 4</u>	-	2	2.4	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	150	μΑ
Dynamic (	characteristics					
Q <sub>r</sub>	recovered charge	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{\text{A}} \text{ and } \frac{6}{\text{A}}$	-	40	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 8 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; see Figure 6	-	12.5	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{\text{A}} \text{ and } \frac{7}{\text{A}}$	-	21	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}$	-	4	5.5	Α

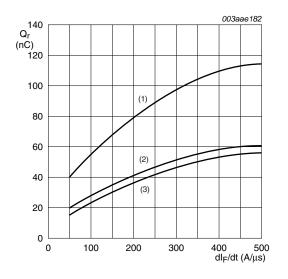


(1)  $T_j = 150$  °C; typical values

(2)  $T_j = 150$  °C; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig 4. Forward current as a function of forward voltage



(1)  $I_F = 16 \text{ A}(2) I_F = 8 \text{ A}(3) I_F = 4 \text{ A}$ 

Fig 5. Recovered charge as a function of rate of change of forward current; Tj = 125 °C; typical values

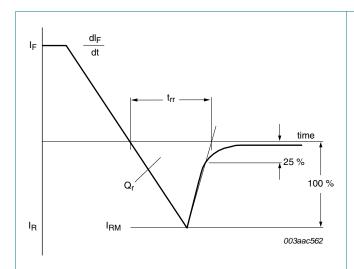


Fig 6. Reverse recovery definitions; ramp recovery

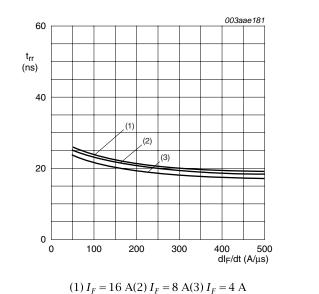


Fig 7. Recovered charge as a function of rate of change of forward current; Tj = 125 °C; typical values

### 8. Package outline

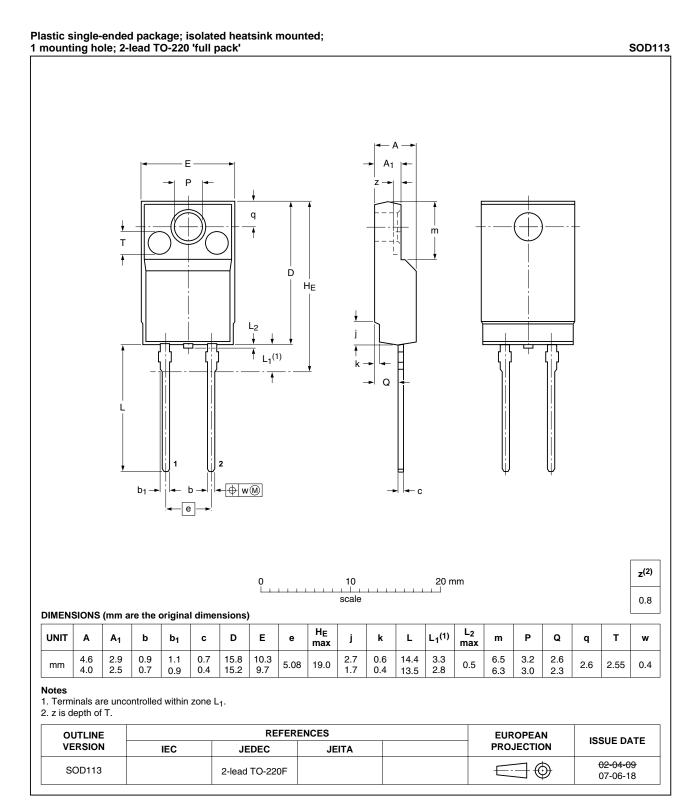


Fig 8. Package outline SOD113 (TO-220F)

BYC58X-600

8 A hyperfast rectifier diode

## 9. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC58X-600_1	20100223	Product data sheet	-	-

### 10. Legal information

#### 10.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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